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(54) ISOTOPIC DIAMOND DOPED WITH BORON AND ITS PRODUCTION

(57)Abstract:

PROBLEM TO BE SOLVED: To produce a 12C or 13C isotopic diamond which has purity of a specified value or higher and thermal conductivity of a specified value or higher and is doped with boron, by adding a specified concn. or lower of boron to a carbon raw material consisting of isotopically purified 12C or 13C, a flux and/or their peripheries, diffusing the carbon raw material in the flux under high temp. and high pressure conditions and growing a single crystal on a seed crystal.

SOLUTION: In the this isotopic diamond, the boron concn. is ≤100 ppm and purity of the isotopic diamond produced is at least \geq 99.5% and the thermal conductivity at room temp. is by \geq 30% higher than that of a high purity diamond having natural isotopic abundance. Preferably, by using a gaseous mixture of a hydrocarbon, carbon monoxide, carbon dioxide or a mixture of at least two of these gases, each of which consists of isotopically purified 12C or 13C, and gaseous hydrogen, as the carbon raw material and also, adding boron as a dopant component, the objective isotopic diamond is formed in a thin-filmy state on a substrate placed in a reactive atmosphere. This isotopic diamond is an excellent material as a material for a device such as semiconductor device or light-emitting device, on which heat is exerted.

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